



# BUK98150-55A

## N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

## 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

## 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

## 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                                    | Conditions                                                                                                                              |  | Min | Typ | Max | Unit |
|-------------------------|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|-----|------|
| V <sub>DS</sub>         | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C                                                                                         |  | -   | -   | 55  | V    |
| I <sub>D</sub>          | drain current                                | V <sub>GS</sub> = 5 V; T <sub>sp</sub> = 25 °C; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>                                         |  | -   | -   | 5.5 | A    |
| P <sub>tot</sub>        | total power dissipation                      | T <sub>sp</sub> = 25 °C; <a href="#">Fig. 1</a>                                                                                         |  | -   | -   | 8   | W    |
| Static characteristics  |                                              |                                                                                                                                         |  |     |     |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance             | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C                                                                   |  | -   | -   | 161 | mΩ   |
|                         |                                              | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C                                                                    |  | -   | 116 | 137 | mΩ   |
|                         |                                              | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                  |  | -   | 128 | 150 | mΩ   |
| Dynamic characteristics |                                              |                                                                                                                                         |  |     |     |     |      |
| Q <sub>GD</sub>         | gate-drain charge                            | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; V <sub>DS</sub> = 44 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a>                    |  | -   | 2.8 | -   | nC   |
| Avalanche ruggedness    |                                              |                                                                                                                                         |  |     |     |     |      |
| E <sub>DS(AL)S</sub>    | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 5.5 A; V <sub>sup</sub> ≤ 55 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped |  | -   | -   | 22  | mJ   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                  | Graphic symbol                                                                                |
|-----|--------|-------------|-----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | G      | gate        | <br>SC-73 (SOT223) | <br>mbb076 |
| 2   | D      | drain       |                                                                                                     |                                                                                               |
| 3   | S      | source      |                                                                                                     |                                                                                               |
| 4   | D      | drain       |                                                                                                     |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number     | Package |                                                                  |         |
|-----------------|---------|------------------------------------------------------------------|---------|
|                 | Name    | Description                                                      | Version |
| BUK98150-55A    | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |
| BUK98150-55A/CU | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |

## 7. Marking

Table 4. Marking codes

| Type number     | Marking code |
|-----------------|--------------|
| BUK98150-55A    | 915055A      |
| BUK98150-55A/CU | 915055       |

## 8. Limiting values

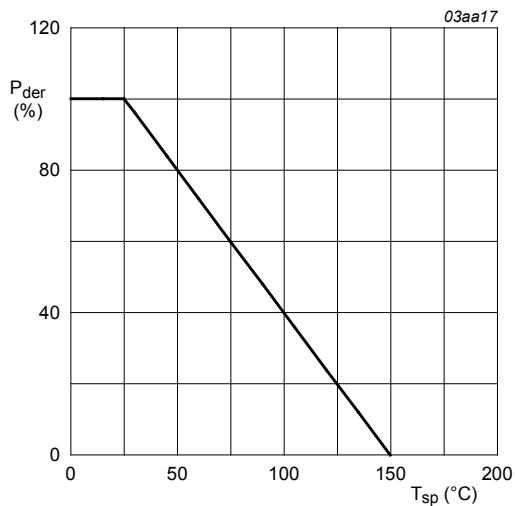
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                                                                                        | Min | Max | Unit |
|-----------|-------------------------|---------------------------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$                                                | -   | 55  | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                                                                      | -   | 55  | V    |
| $V_{GS}$  | gate-source voltage     |                                                                                                   | -15 | 15  | V    |
| $P_{tot}$ | total power dissipation | $T_{sp} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                  | -   | 8   | W    |
| $I_D$     | drain current           | $T_{sp} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | 5.5 | A    |
|           |                         | $T_{sp} = 100\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 2</a>                         | -   | 3   | A    |
| $I_{DM}$  | peak drain current      | $T_{sp} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 3</a>       | -   | 22  | A    |

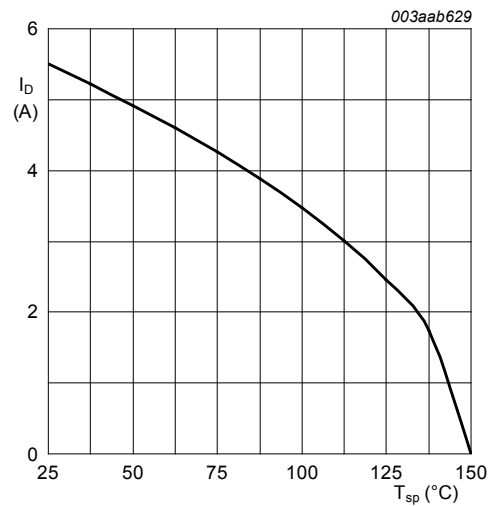
| Symbol                      | Parameter                                    | Conditions                                                                                                                                                                     |                              | Min | Max | Unit |
|-----------------------------|----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------|-----|-----|------|
| $T_{\text{stg}}$            | storage temperature                          |                                                                                                                                                                                |                              | -55 | 150 | °C   |
| $T_j$                       | junction temperature                         |                                                                                                                                                                                |                              | -55 | 150 | °C   |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                                                |                              |     |     |      |
| $I_S$                       | source current                               | $T_{\text{sp}} = 25\text{ °C}$                                                                                                                                                 |                              | -   | 5.5 | A    |
| $I_{\text{SM}}$             | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{\text{sp}} = 25\text{ °C}$                                                                                                      |                              | -   | 22  | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                                |                              |     |     |      |
| $E_{\text{DS(AL)S}}$        | non-repetitive drain-source avalanche energy | $I_D = 5.5\text{ A}$ ; $V_{\text{sup}} \leq 55\text{ V}$ ; $R_{\text{GS}} = 50\text{ }\Omega$ ; $V_{\text{GS}} = 5\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; unclamped |                              | -   | 22  | mJ   |
| $E_{\text{DS(AL)R}}$        | repetitive drain-source avalanche energy     | <a href="#">Fig. 4</a>                                                                                                                                                         | <a href="#">[1][2][3][4]</a> | -   |     | J    |

- [1] Value not quoted. Repetitive rating defined in avalanche rating figure.  
 [2] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.  
 [3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.  
 [4] Refer to application note AN10273 for further information.



**Fig. 1. Normalized total power dissipation as a function of solder point temperature**

$$P_{\text{der}} = \frac{P_{\text{tot}}}{P_{\text{tot}(25^\circ\text{C})}} \times 100\%$$



**Fig. 2. Continuous drain current as a function of solder point temperature**

$$V_{\text{GS}} \geq 5\text{ V}$$

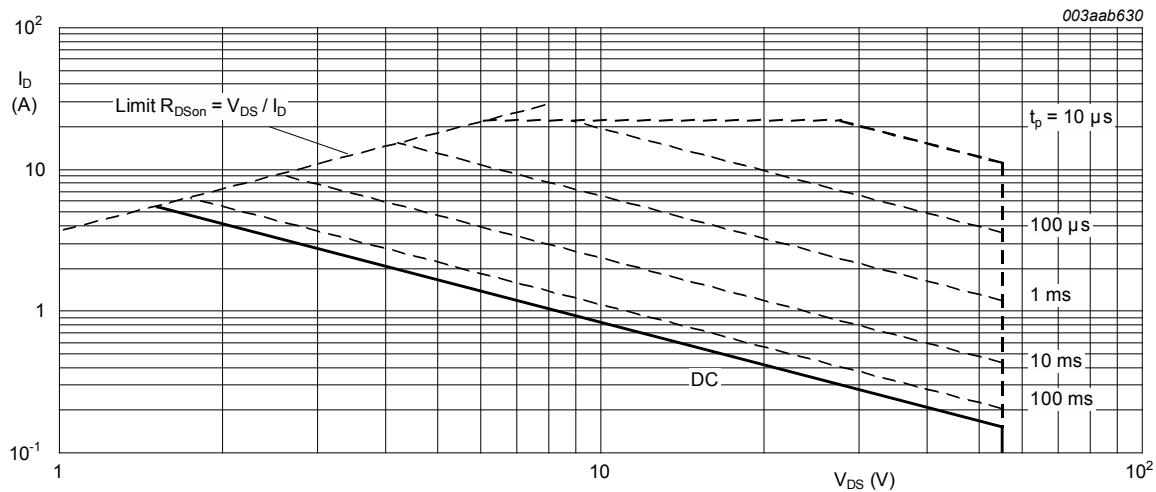


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25\text{ }^{\circ}\text{C}; I_{DM}$  is single pulse

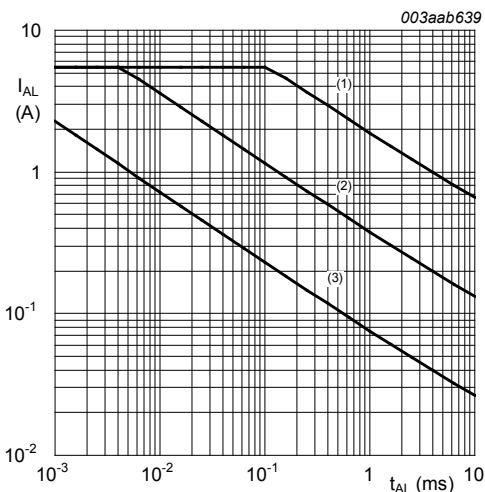


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

- (1) Single-pulse;  $T_j = 25\text{ }^{\circ}\text{C}$ .
- (2) Single-pulse;  $T_j = 125\text{ }^{\circ}\text{C}$ .
- (3) Repetitive.

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                        | Conditions | Min | Typ | Max | Unit |
|----------------|--------------------------------------------------|------------|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | Fig. 5     | -   | -   | 15  | K/W  |

| Symbol        | Parameter                                         | Conditions |  | Min | Typ | Max | Unit |
|---------------|---------------------------------------------------|------------|--|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance<br>from junction to<br>ambient |            |  | -   | 120 | -   | K/W  |

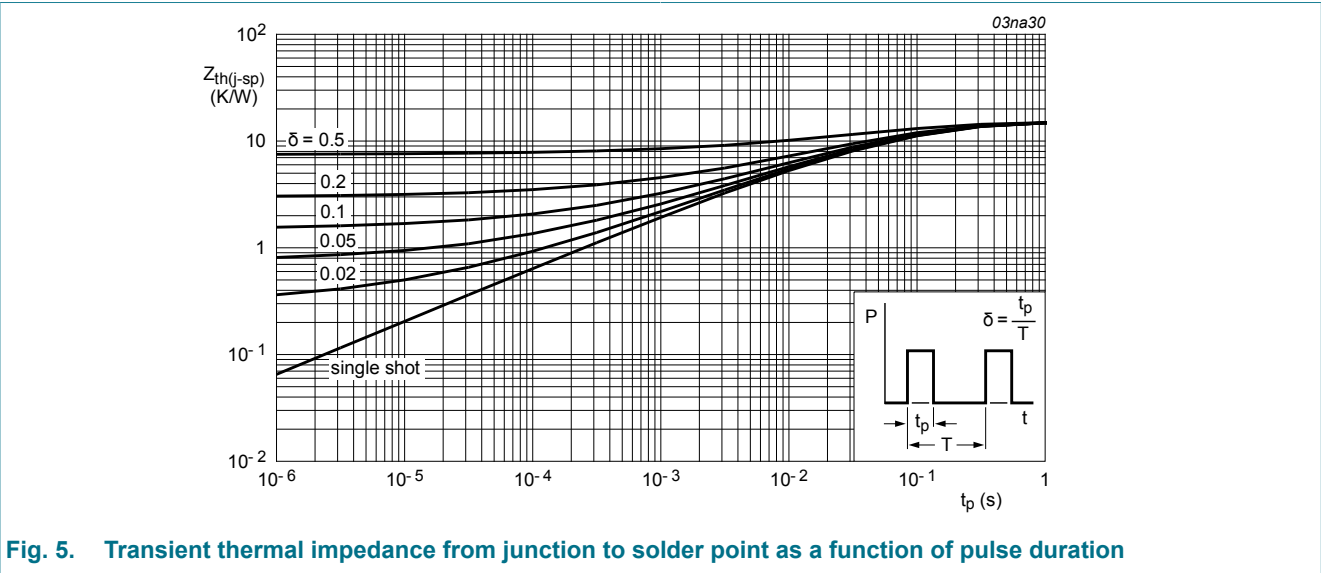


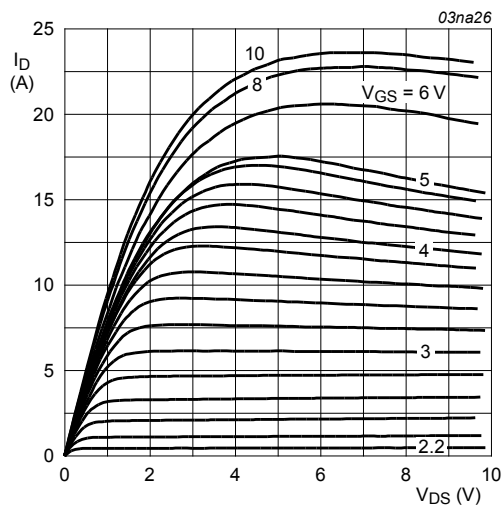
Fig. 5. Transient thermal impedance from junction to solder point as a function of pulse duration

10. Characteristics

Table 7. Characteristics

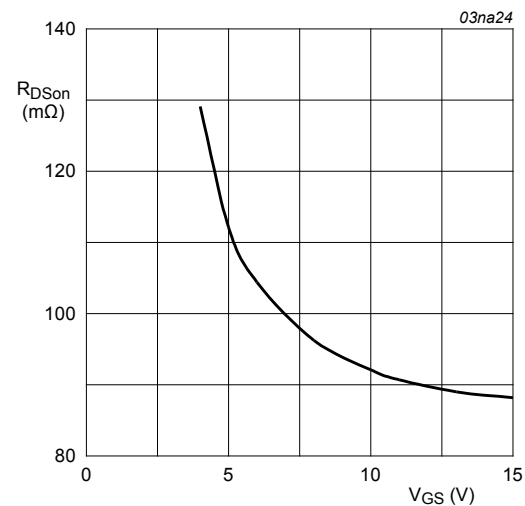
| Symbol                 | Parameter                           | Conditions                                                                                                                              |  | Min | Typ  | Max | Unit          |
|------------------------|-------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|---------------|
| Static characteristics |                                     |                                                                                                                                         |  |     |      |     |               |
| $V_{(BR)DSS}$          | drain-source<br>breakdown voltage   | $I_D = 0.25\text{ mA}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -55\text{ }^{\circ}\text{C}$                                                    |  | 50  | -    | -   | V             |
|                        |                                     | $I_D = 0.25\text{ mA}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                                                     |  | 55  | -    | -   | V             |
| $V_{GS(th)}$           | gate-source threshold<br>voltage    | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ;<br><a href="#">Fig. 11</a>                               |  | 1   | 1.5  | 2   | V             |
|                        |                                     | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ;<br><a href="#">Fig. 11</a>                              |  | 0.6 | -    | -   | V             |
|                        |                                     | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\text{ }^{\circ}\text{C}$ ;<br><a href="#">Fig. 11</a>                              |  | -   | -    | 2.3 | V             |
| $I_{DSS}$              | drain leakage current               | $V_{DS} = 55\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                                                     |  | -   | 0.05 | 10  | $\mu\text{A}$ |
|                        |                                     | $V_{DS} = 55\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$                                                    |  | -   | -    | 500 | $\mu\text{A}$ |
| $I_{GSS}$              | gate leakage current                | $V_{GS} = 15\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                                                     |  | -   | 2    | 100 | nA            |
|                        |                                     | $V_{GS} = -15\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                                                    |  | -   | 2    | 100 | nA            |
| $R_{DSon}$             | drain-source on-state<br>resistance | $V_{GS} = 5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ;<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> |  | -   | -    | 276 | m $\Omega$    |
|                        |                                     | $V_{GS} = 4.5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                                                       |  | -   | -    | 161 | m $\Omega$    |
|                        |                                     | $V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                                                        |  | -   | 116  | 137 | m $\Omega$    |

| Symbol                  | Parameter                    | Conditions                                                                                                                                                  |  | Min | Typ  | Max | Unit |
|-------------------------|------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
|                         |                              | $V_{GS} = 5\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                         |  | -   | 128  | 150 | mΩ   |
| Dynamic characteristics |                              |                                                                                                                                                             |  |     |      |     |      |
| $Q_{G(\text{tot})}$     | total gate charge            | $I_D = 5\text{ A}$ ; $V_{DS} = 44\text{ V}$ ; $V_{GS} = 5\text{ V}$ ;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 14</a>                       |  | -   | 5.3  | -   | nC   |
| $Q_{GS}$                | gate-source charge           |                                                                                                                                                             |  | -   | 1    | -   | nC   |
| $Q_{GD}$                | gate-drain charge            |                                                                                                                                                             |  | -   | 2.8  | -   | nC   |
| $C_{iss}$               | input capacitance            | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 15</a>                       |  | -   | 240  | 320 | pF   |
| $C_{oss}$               | output capacitance           |                                                                                                                                                             |  | -   | 53   | 64  | pF   |
| $C_{rss}$               | reverse transfer capacitance |                                                                                                                                                             |  | -   | 40   | 55  | pF   |
| $t_{d(\text{on})}$      | turn-on delay time           | $V_{DS} = 20\text{ V}$ ; $R_L = 3.3\text{ }\Omega$ ; $V_{GS} = 5\text{ V}$ ;<br>$R_{G(\text{ext})} = 10\text{ }\Omega$ ; $T_j = 25\text{ }^{\circ}\text{C}$ |  | -   | 8    | -   | ns   |
| $t_r$                   | rise time                    |                                                                                                                                                             |  | -   | 57   | -   | ns   |
| $t_{d(\text{off})}$     | turn-off delay time          |                                                                                                                                                             |  | -   | 16   | -   | ns   |
| $t_f$                   | fall time                    |                                                                                                                                                             |  | -   | 13   | -   | ns   |
| Source-drain diode      |                              |                                                                                                                                                             |  |     |      |     |      |
| $V_{SD}$                | source-drain voltage         | $I_S = 5\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 16</a>                                                   |  | -   | 0.85 | 1.2 | V    |
| $t_{rr}$                | reverse recovery time        | $I_S = 5\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ;<br>$V_{GS} = -10\text{ V}$ ; $V_{DS} = 30\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$       |  | -   | 24   | -   | ns   |
| $Q_r$                   | recovered charge             |                                                                                                                                                             |  | -   | 30   | -   | nC   |



**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**

$T_j = 25^{\circ}\text{C}$ ;  $t_p = 300\mu\text{s}$



**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25^{\circ}\text{C}$ ;  $I_D = 5\text{ A}$

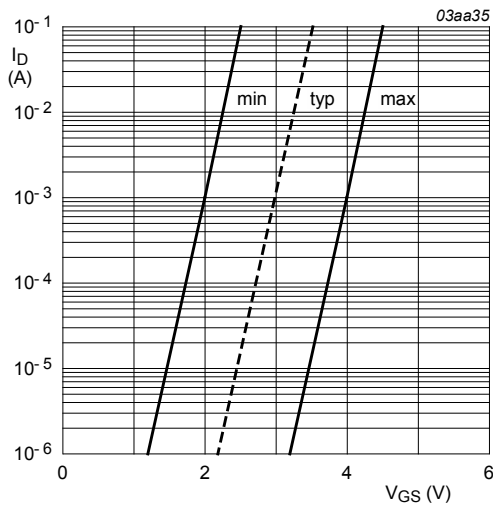


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$T_J = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

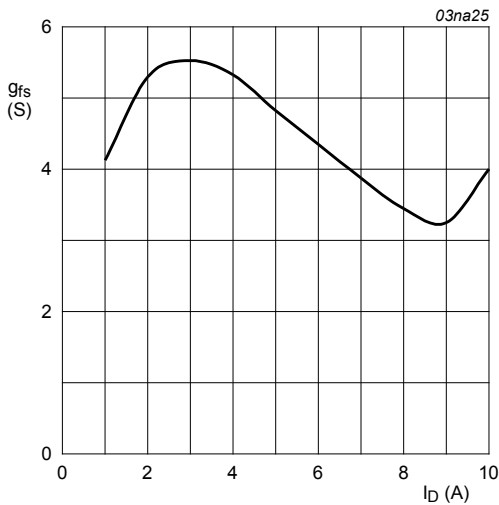


Fig. 9. Forward transconductance as a function of drain current; typical values

$T_J = 25\text{ }^{\circ}\text{C}; V_{DS} = 25\text{ V}$

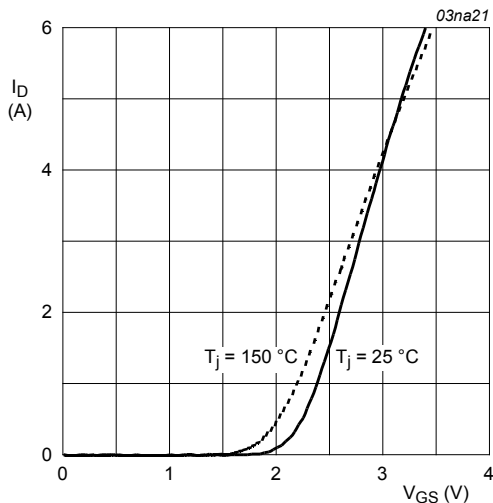


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 25\text{ V}$

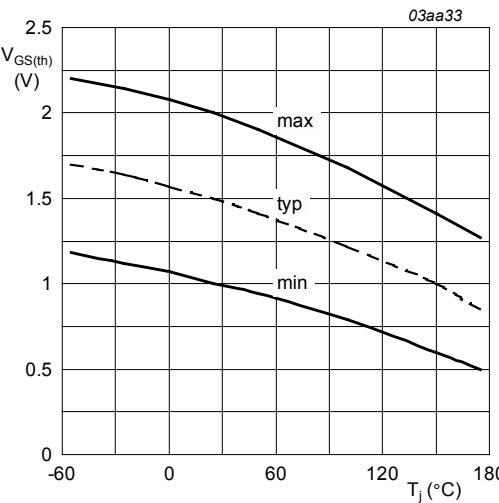


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

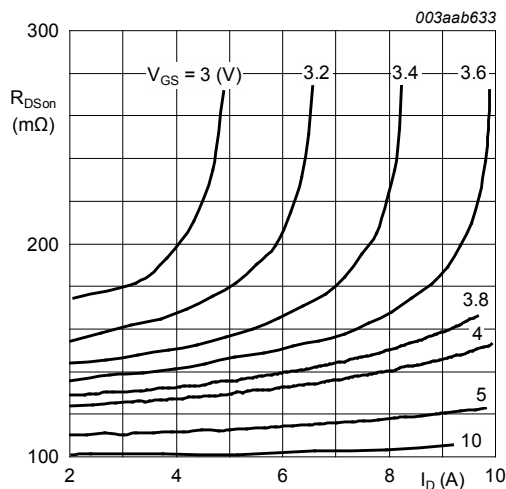


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\text{ }^{\circ}\text{C}$$

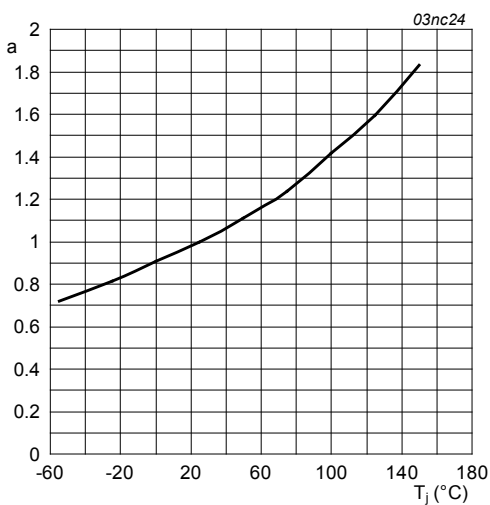


Fig. 13. Normalized drain source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)25^{\circ}\text{C}}}$$

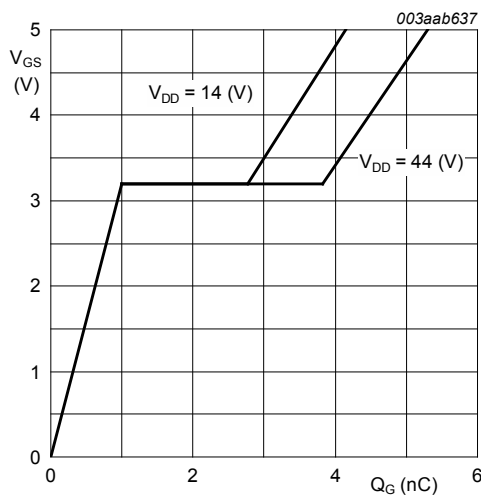


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\text{ }^{\circ}\text{C}; I_D = 5\text{ A}$$

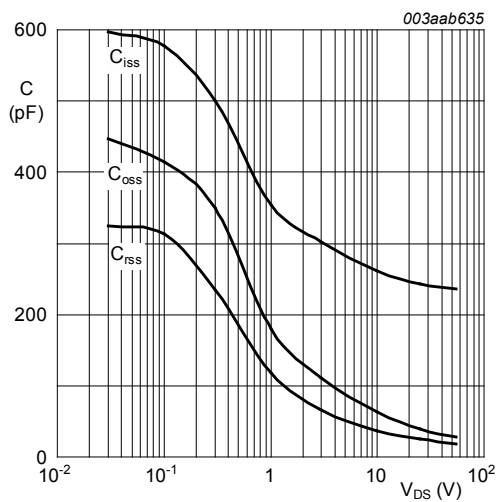


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$

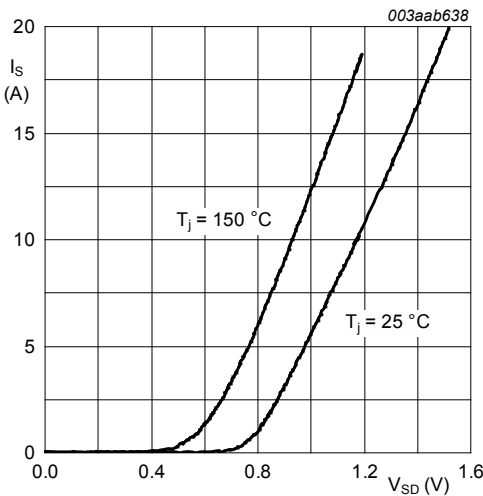


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline

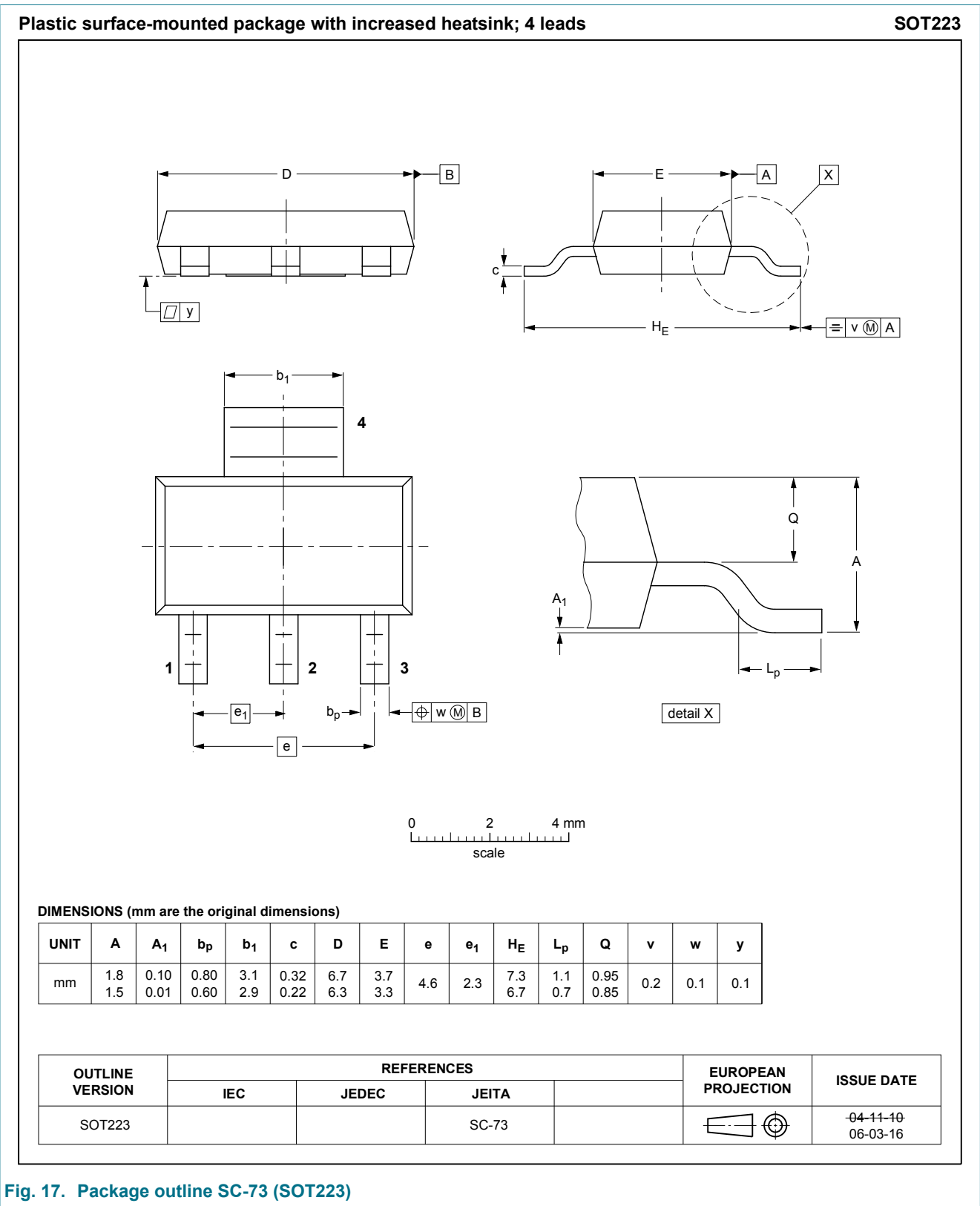


Fig. 17. Package outline SC-73 (SOT223)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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13. Contents

1 General description ..... 1

2 Features and benefits ..... 1

3 Applications ..... 1

4 Quick reference data ..... 1

5 Pinning information ..... 2

6 Ordering information ..... 2

7 Marking ..... 2

8 Limiting values ..... 2

9 Thermal characteristics ..... 4

10 Characteristics ..... 5

11 Package outline ..... 10

12 Legal information ..... 11

12.1 Data sheet status ..... 11

12.2 Definitions ..... 11

12.3 Disclaimers ..... 11

12.4 Trademarks ..... 12

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